

Die: 3.1mmx1.45mmx0.102mm



Product Description

RFMD's SDA-1000 is a directly coupled (DC) GaAs microwave monolithic integrated circuit (MMIC) distributed driver amplifier die designed to support a wide array of high frequency commercial, military, and space applications. They are ideal for wideband amplifier gain blocks, broadband test equipment (ATE), military, and aerospace applications.

Features

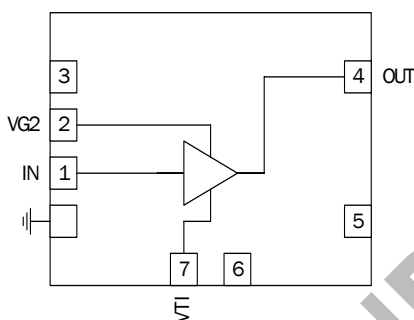
- DC to 20GHz Operation
- +26dBm P_{SAT}
- Gain = 14 dB Typical
- Noise Figure = 4 dB
- Output Voltage to 8V_{PP}
- 300 mA Total Current

Applications

- Military
- Aerospace
- Broadband ATE
- Instrumentation

Optimum Technology Matching® Applied

- GaAs HBT
- GaAs MESFET
- InGaP HBT
- SiGe BiCMOS
- Si BiCMOS
- SiGe HBT
- GaAs pHEMT
- Si CMOS
- Si BJT
- GaN HEMT
- InP HBT
- RF MEMS
- LDMOS



Parameter	Specification			Unit	Condition
	Min.	Typ.	Max.		
Electrical Specifications					T _A = +25 °C, V _{DD} = +8V _{DC} , VG2 at = +1.5V _{DC} , I _{DD} = 300 mA
Operating Frequency	DC		20	GHz	
Gain		14		dB	
Output Voltage	4		8	V _{P-P}	
IP3 at 10GHz		36		dBm	P _{OUT} ≅ +10 dBm
P1dB at 10GHz		25		dBm	
P _{SAT} at 10GHz		26.5		dBm	
Noise Figure at Mid-Band		4		dB	
Input Return Loss	10	15		dB	
Output Return Loss	13	15			
Supply Current		300		mA	
Supply Voltage		8		V _{DC}	

*Adjust VTI between -1.5V_{DC} to +0.2V_{DC} to achieve I_{DD} = 300mA typical.

**Please contact
RFMD Technical Support
at (336) 678-5570
for more information.**

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